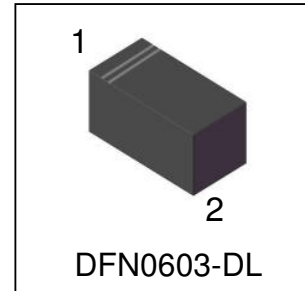


LESD11LL3.3T5G ESD PROTECTION DIODE

Discription

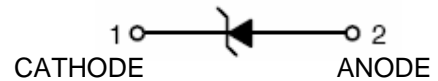
The LESD11LL3.3T5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.

LESD11LL3.3T5G



Applications

- I Cellular phones audio
- I Digital cameras
- I Portable applications
- I Mobile telephone



Features

- I Small Body Outline Dimensions: 0.61 mm x 0.31 mm
- I Low Body Height: 0.28 mm
- I Low Leakage
- I Response Time is Typically < 1 ns
- I ESD Rating of Class 3 per Human Body Model
- I IEC61000-4-2 Level 4 ESD Protection
- I These are Pb-Free Devices
- I We declare that the material of product compliance with RoHS requirements and Halogen Free.

Ordering information

Device	Package	Shipping
LESD11LL3.3T5G	DFN0603	15000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		±16 ±16	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T _A =25°C	PD	200	mW
Junction and Storage Temperature Range	T _J ,T _{STG}	-55 to 150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

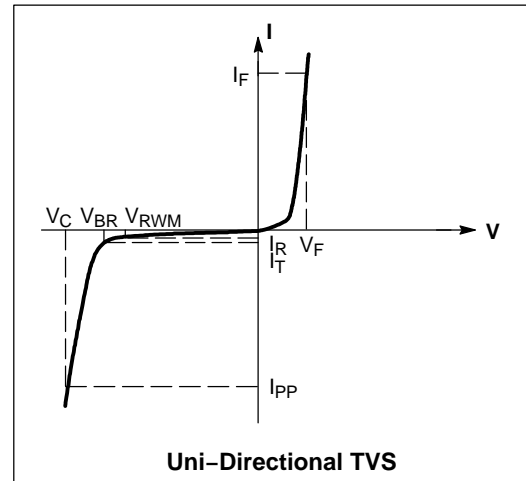
1. FR-5 = 1.0*0.75*0.62 in.

LESD11LL3.3T5G

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Capacitance @ $V_R = 0$ and $f = 1.0$ MHz



ELECTRICAL CHARACTERISTICS

Device	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ $I_T = 1$ mA (Note 1)		V_C (V) @ $I_{PP} = 1$ A (Note 2)	V_C (V) @ MAX I_{PP} (Note 2)	I_{PF} (A) (Note 2)	P_{PK} (W) (Note 2)	C (pF)	
	Max	Max	Min	Max	Max	Max	Max	Max	Typ	Max
LESD11LL3.3T5G	3.3	0.5	4.5	7.8	10	14	5	70	0.5	0.6

Other voltage available upon request.

- V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C
- Surge current waveform per Figure 1.

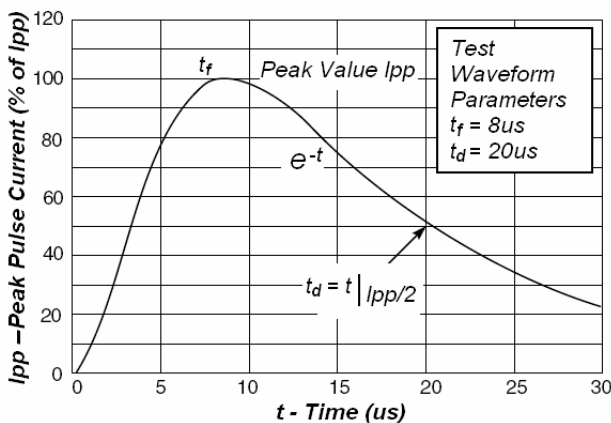


Fig1. Pulse Waveform

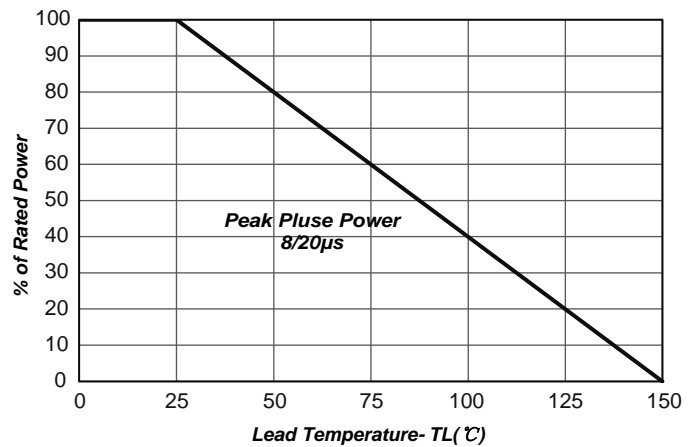
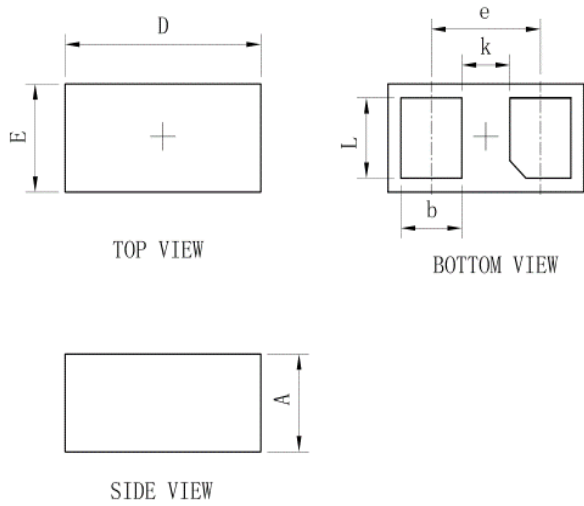


Fig2. Power Derating Curve

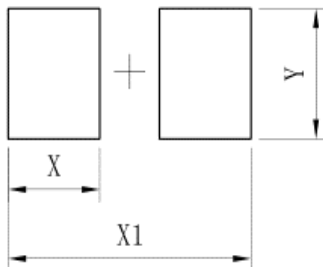
LESD11LL3.3T5G

OUTLINE AND DIMENSIONS



DFN0603-DL			
Dim	Min	Typ.	Max
D	0.58	0.61	0.64
E	0.28	0.31	0.34
e	-	0.34	-
L	0.20	0.23	0.26
b	0.16	0.19	0.22
A	0.25	0.28	0.31
k	0.12	0.15	0.18
All Dimensions in mm			

SOLDERING FOOTPRINT



DFN0603-DL	
DIM	(mm)
X	0.23
X1	0.61
Y	0.30

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)